

PZT3904T1G

General Purpose Transistor

NPN Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	200	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

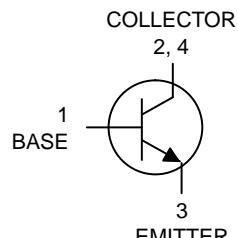
Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) $T_A = 25^\circ\text{C}$	P_D	1.5 12	W mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	83.3	$^\circ\text{C}/\text{W}$
Thermal Resistance Junction-to-Lead #4	$R_{\theta JA}$	35	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-4 with 1 oz and 713 mm² of copper area.



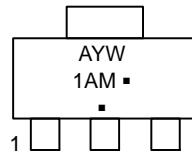
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<http://onsemi.com>



SOT-223
CASE 318E
STYLE 1

MARKING DIAGRAM



1AM = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
PZT3904T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
SPZT3904T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PZT3904T1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS (Note 2)				
Collector-Emitter Breakdown Voltage (Note 3) ($I_C = 1.0 \text{ mA}, I_B = 0$)	$V_{(\text{BR})\text{CEO}}$	40	–	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{A}, I_E = 0$)	$V_{(\text{BR})\text{CBO}}$	60	–	
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{A}, I_C = 0$)	$V_{(\text{BR})\text{EBO}}$	6.0	–	
Base Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc}$)	I_{BL}	–	50	nAdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc}$)	I_{CEX}	–	50	

ON CHARACTERISTICS (Note 3)

DC Current Gain (Note 2) ($I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ Vdc}$)	H_{FE}	40 70 100 60 30	– – 300 – –	–
Collector-Emitter Saturation Voltage (Note 3) ($I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$) ($I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$)	$V_{CE(\text{sat})}$	– –	0.2 0.3	Vdc
Base-Emitter Saturation Voltage (Note 3) ($I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$) ($I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$)	$V_{BE(\text{sat})}$	0.65 –	0.85 0.95	Vdc

SMALL-SIGNAL CHARACTERISTICS

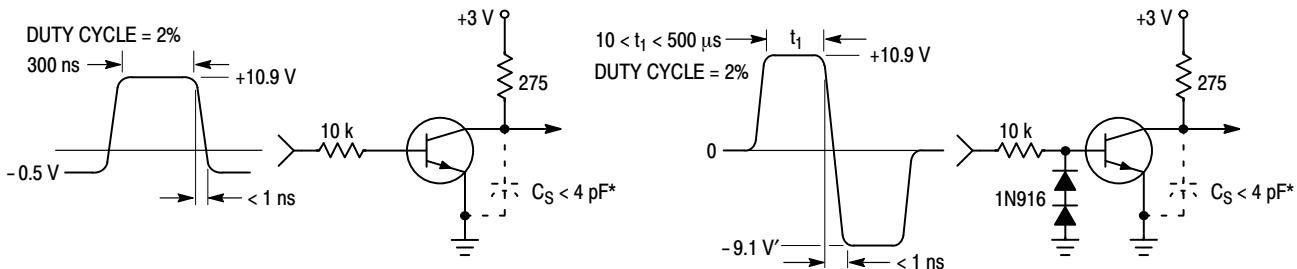
Current-Gain - Bandwidth Product ($I_C = 10 \text{ mA}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz}$)	f_T	300	–	MHz
Output Capacitance ($V_{CB} = 5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C_{obo}	–	5.0	pF
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$)	C_{ibo}	–	8.0	
Input Impedance ($V_{CE} = 10 \text{ Vdc}, I_C = 1.0 \text{ mA}, f = 1.0 \text{ kHz}$)	h_{ie}	1.0	10	k Ω
Voltage Feedback Ratio ($V_{CE} = 10 \text{ Vdc}, I_C = 1.0 \text{ mA}, f = 1.0 \text{ kHz}$)	h_{re}	0.5	8.0	$\times 10^{-4}$
Small-Signal Current Gain ($V_{CE} = 10 \text{ Vdc}, I_C = 1.0 \text{ mA}, f = 1.0 \text{ kHz}$)	h_{fe}	100	400	–
Output Admittance ($V_{CE} = 10 \text{ Vdc}, I_C = 1.0 \text{ mA}, f = 1.0 \text{ kHz}$)	h_{oe}	1.0	40	μMhos
Noise Figure ($V_{CE} = 5.0 \text{ Vdc}, I_C = 100 \mu\text{A}, R_S = 1.0 \text{ k}\Omega, f = 1.0 \text{ kHz}$)	nF	–	5.0	dB

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 3.0 \text{ Vdc}, V_{BE} = -0.5 \text{ Vdc}, I_C = 10 \text{ mA}, I_{B1} = 1.0 \text{ mA})$	t_d	–	35	ns
Rise Time		t_r	–	35	
Storage Time		t_s	–	200	
Fall Time		t_f	–	50	

2. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.



* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time
Equivalent Test Circuit

Figure 2. Storage and Fall Time
Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

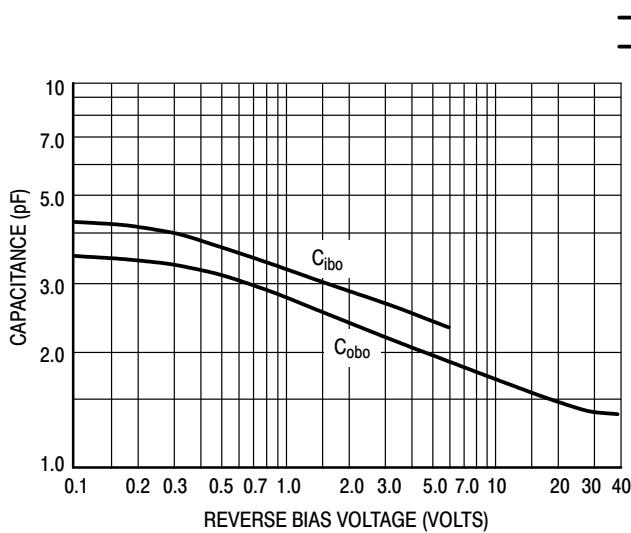


Figure 3. Capacitance

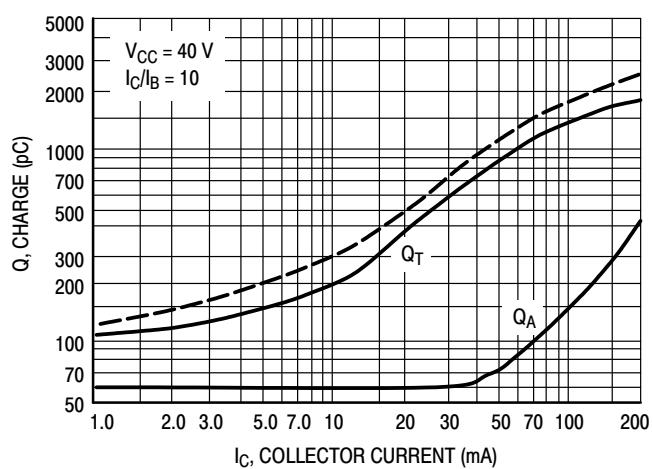


Figure 4. Charge Data

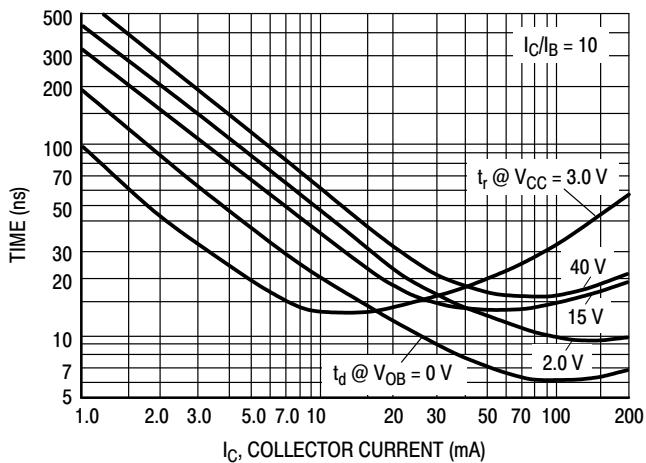


Figure 5. Turn-On Time

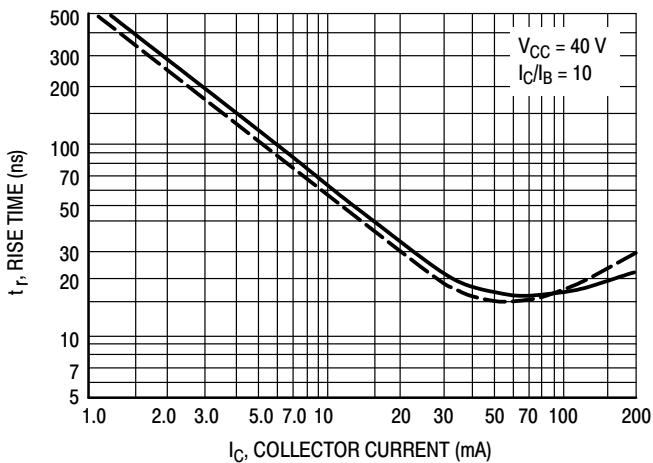


Figure 6. Rise Time

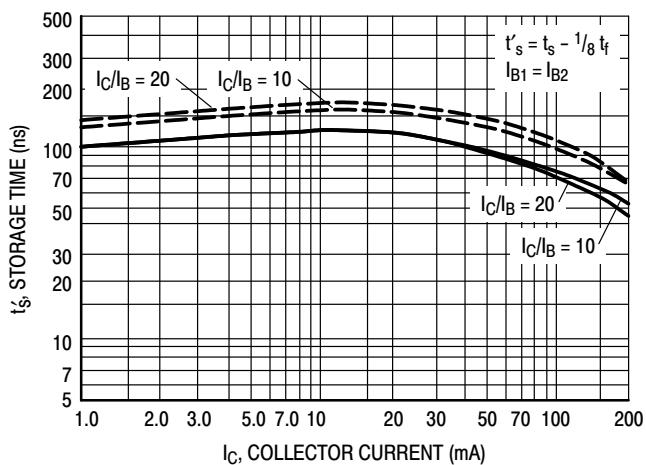


Figure 7. Storage Time

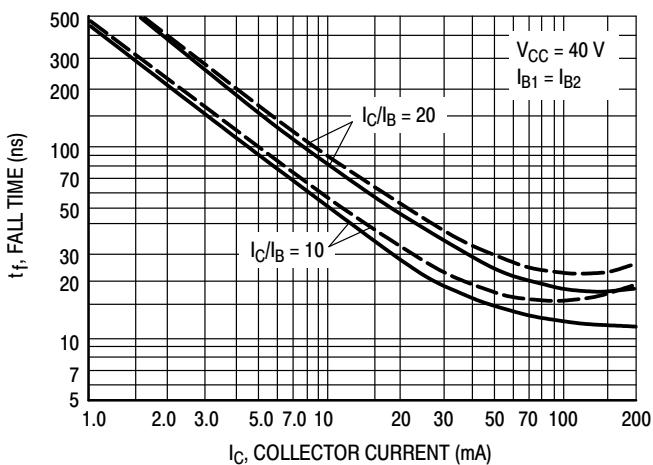


Figure 8. Fall Time

PZT3904T1G

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = 5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

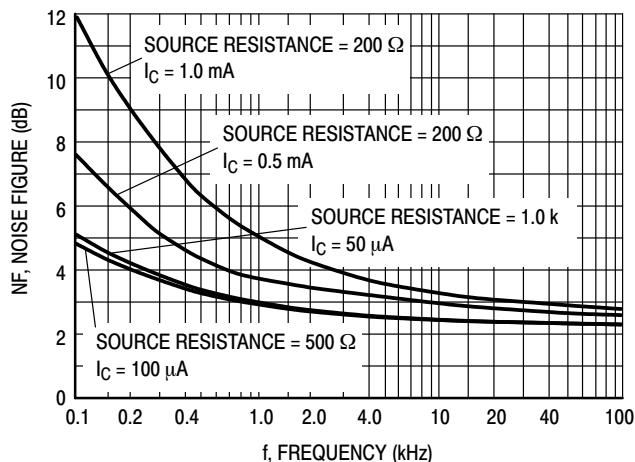


Figure 9.

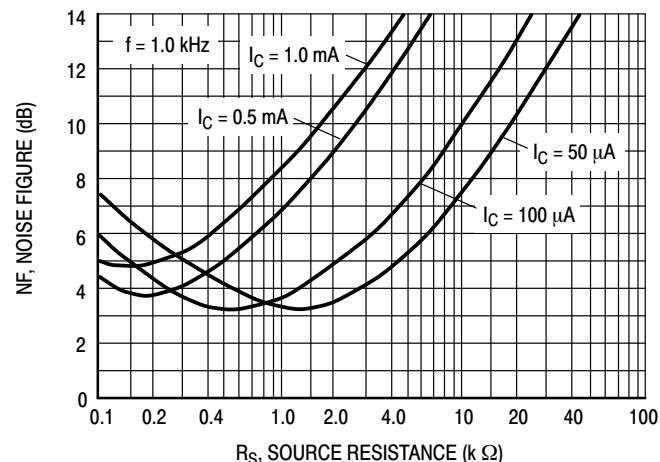


Figure 10.

h PARAMETERS

($V_{CE} = 10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

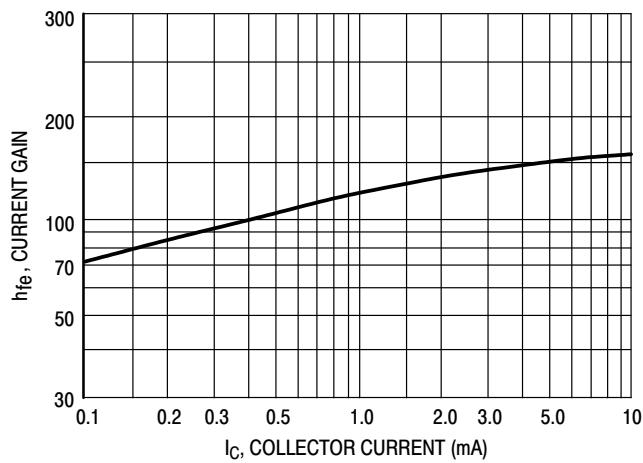


Figure 11. Current Gain

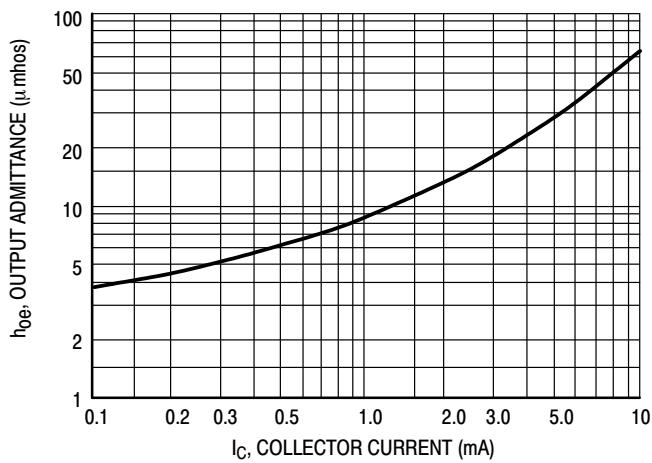


Figure 12. Output Admittance

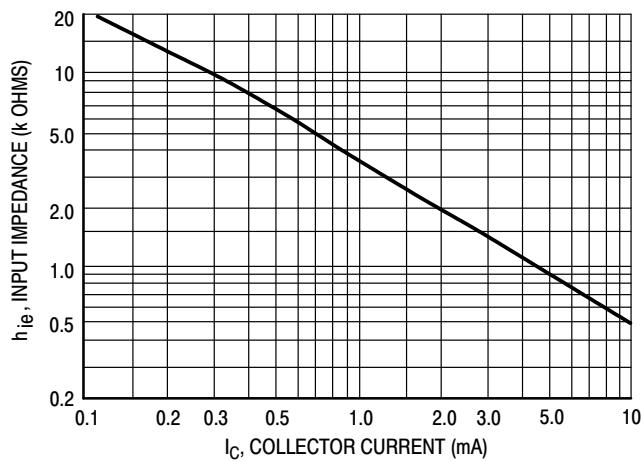


Figure 13. Input Impedance

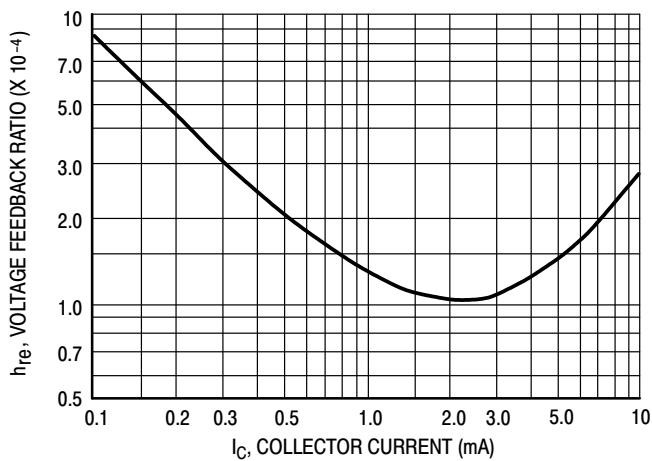


Figure 14. Voltage Feedback Ratio

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TYPICAL STATIC CHARACTERISTICS

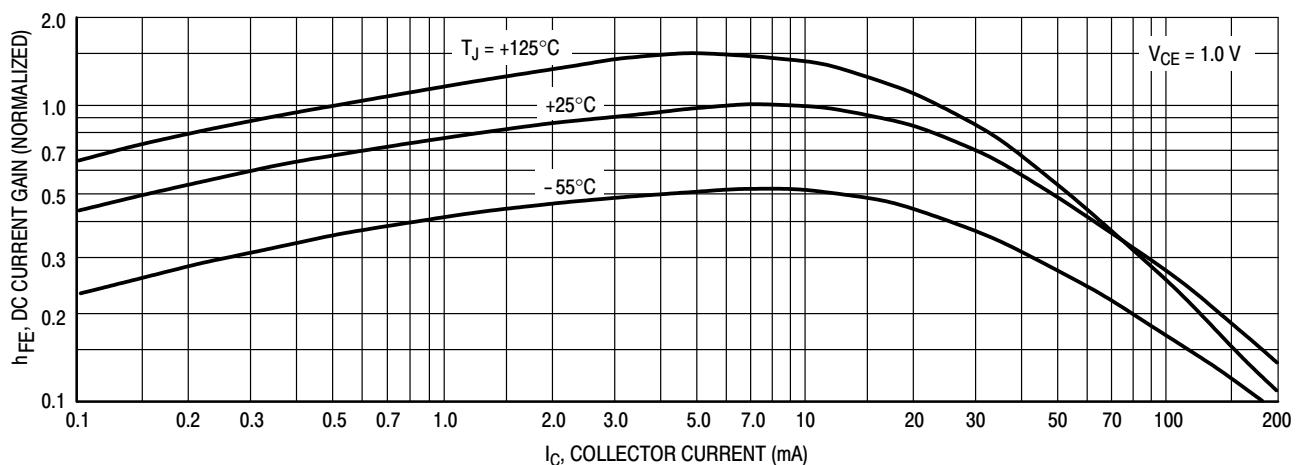


Figure 15. DC Current Gain

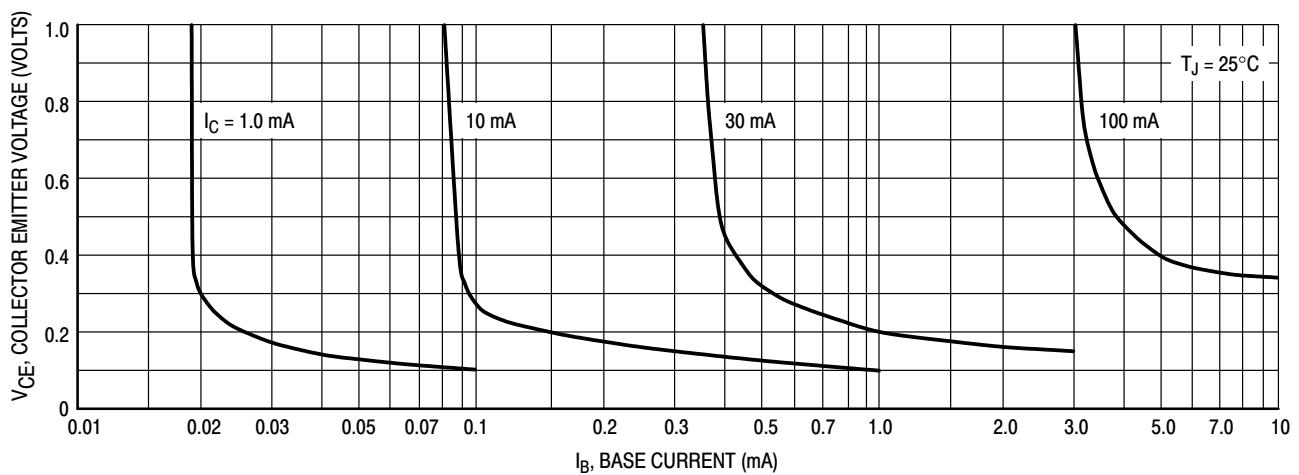


Figure 16. Collector Saturation Region

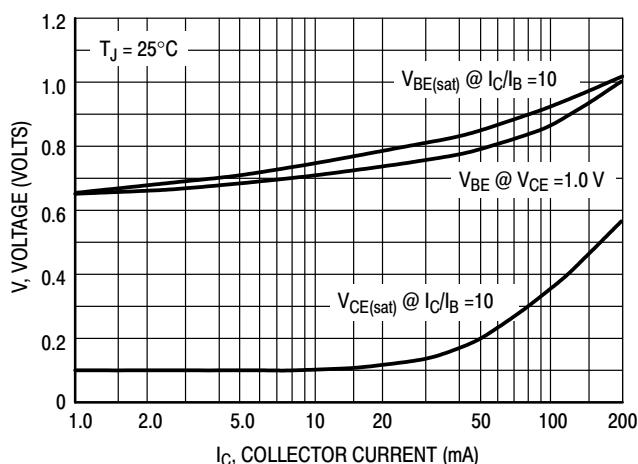


Figure 17. "ON" Voltages

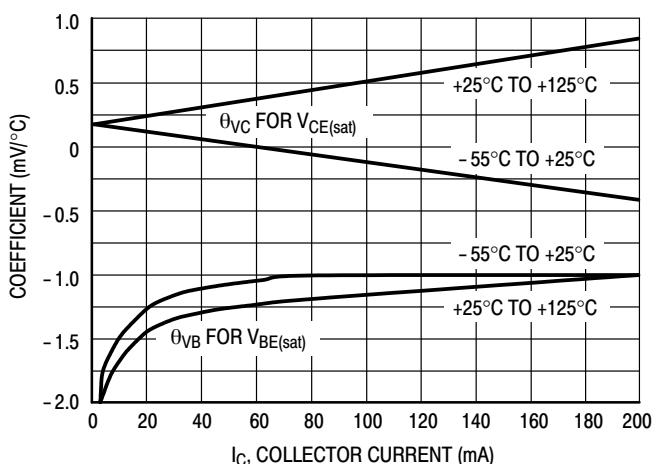


Figure 18. Temperature Coefficients

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TYPICAL CHARACTERISTICS

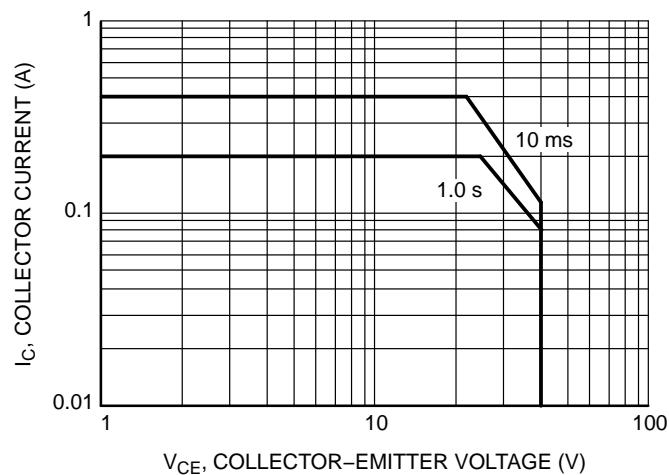


Figure 19. Safe Operating Area

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

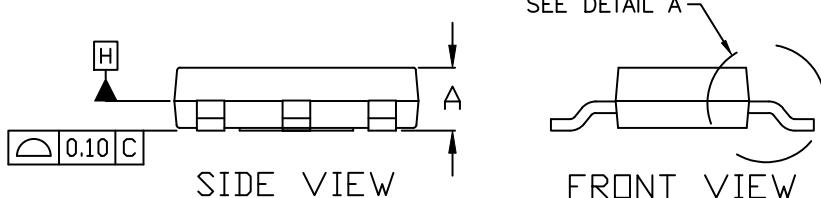
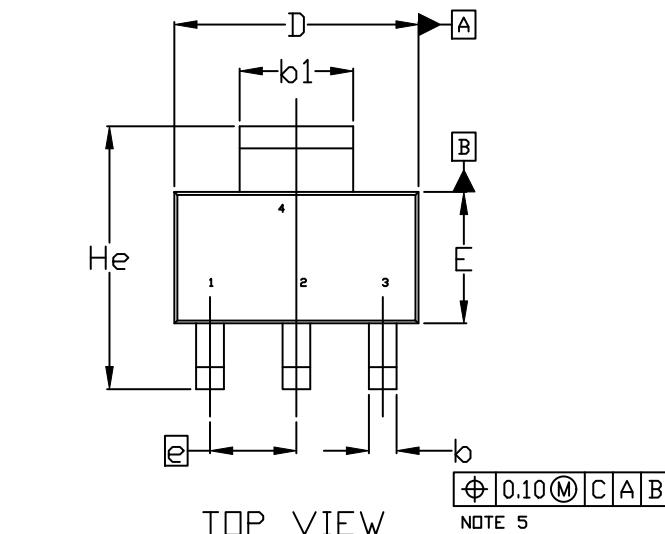
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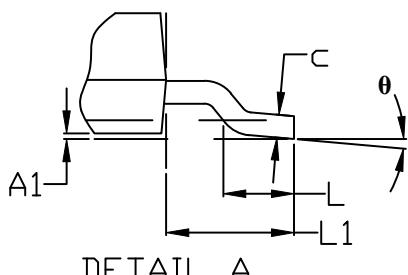
SCALE 1:1

SOT-223 (TO-261)
CASE 318E-04
ISSUE R

DATE 02 OCT 2018



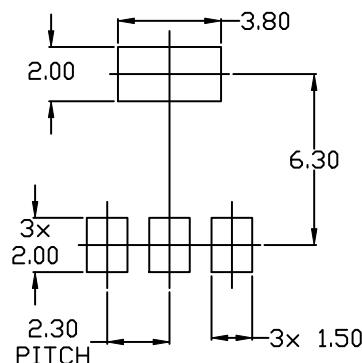
FRONT VIEW



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
θ	0°	---	10°



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SOT-223 (TO-261)

CASE 318E-04

ISSUE R

DATE 02 OCT 2018

STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. Emitter
 4. COLLECTOR

STYLE 2:
 PIN 1. ANODE
 2. CATHODE
 3. NC
 4. CATHODE

STYLE 3:
 PIN 1. GATE
 2. DRAIN
 3. SOURCE
 4. DRAIN

STYLE 4:
 PIN 1. SOURCE
 2. DRAIN
 3. GATE
 4. DRAIN

STYLE 5:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE
 4. GATE

STYLE 6:
 PIN 1. RETURN
 2. INPUT
 3. OUTPUT
 4. INPUT

STYLE 7:
 PIN 1. ANODE 1
 2. CATHODE
 3. ANODE 2
 4. CATHODE

STYLE 8: CANCELLED

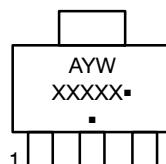
STYLE 9:
 PIN 1. INPUT
 2. GROUND
 3. LOGIC
 4. GROUND

STYLE 10:
 PIN 1. CATHODE
 2. ANODE
 3. GATE
 4. ANODE

STYLE 11:
 PIN 1. MT 1
 2. MT 2
 3. GATE
 4. MT 2

STYLE 12:
 PIN 1. INPUT
 2. OUTPUT
 3. NC
 4. OUTPUT

STYLE 13:
 PIN 1. GATE
 2. COLLECTOR
 3. Emitter
 4. COLLECTOR

**GENERIC
MARKING DIAGRAM***


A = Assembly Location

Y = Year

W = Work Week

XXXXX = Specific Device Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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